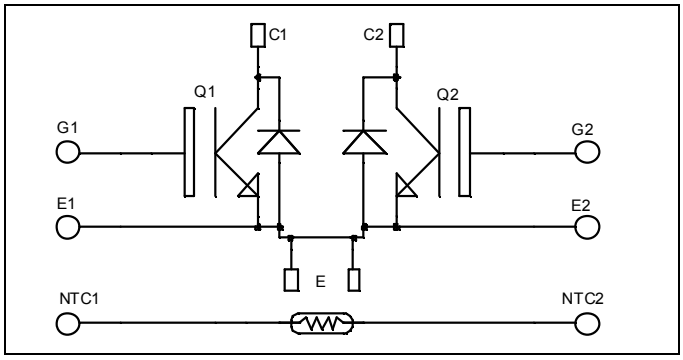
APTGT150DU120T

Dual common source Fast Trench + Field Stop IGBT® Power Module

V_{CES} = 1200V
I_C = 150A @ Tc = 80°C

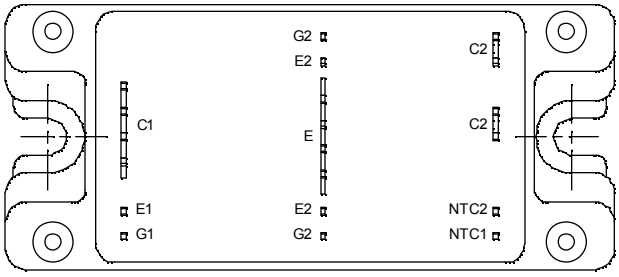


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Fast Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	220	A
		T_C = 80°C	150	
I_{CM}	Pulsed Collector Current	T_C = 25°C	350	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	690	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	300A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1200V				350	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} = 15V, I_C = 150A	T_j = 25°C		1.7	2.1	V
			T_j = 125°C		2.0		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 3 mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				600	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz		10.7		nF
C_{oes}	Output Capacitance			0.56		
C_{res}	Reverse Transfer Capacitance			0.48		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 150A R_G = 2.2Ω		280		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			450		
T_f	Fall Time			75		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 150A R_G = 2.2Ω		290		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			550		
T_f	Fall Time			90		
E_{on}	Turn-on Switching Energy			14		mJ
E_{off}	Turn-off Switching Energy			16		

Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	Tc = 80°C		150		A
V_F	Diode Forward Voltage	I_F = 150A	T_j = 25°C		1.6	2.1	V
			T_j = 125°C		1.6		
t_{rr}	Reverse Recovery Time	I_F = 150A V_R = 600V di/dt =3000A/µs	T_j = 25°C		170		ns
			T_j = 125°C		280		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		15		µC
			T_j = 125°C		29		

Temperature sensor NTC (see application note APT0406 on www.advancedpower.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		kΩ
$B_{25/85}$	T_{25} = 298.15 K		3952		K

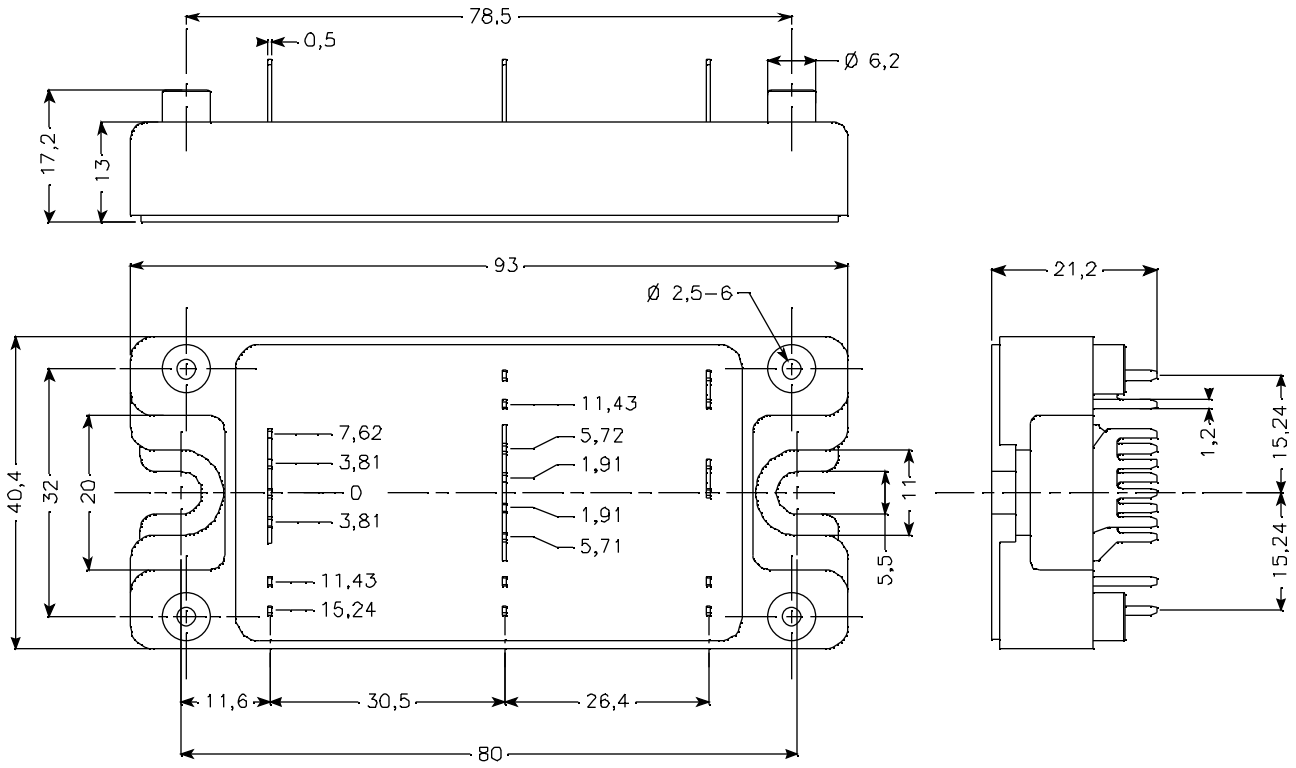
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

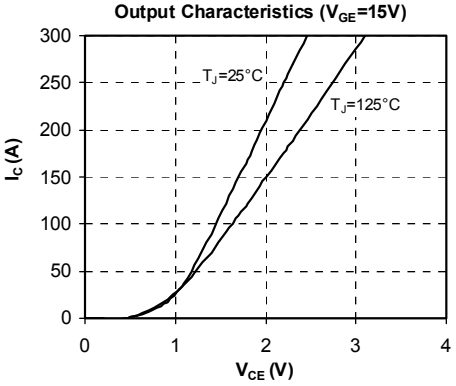
Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case		IGBT			0.18	°C/W
			Diode			0.32	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		125	
Torque	Mounting torque	To Heatsink	M5	1.5		4.7	N.m
Wt	Package Weight					160	g

Package outline (dimensions in mm)

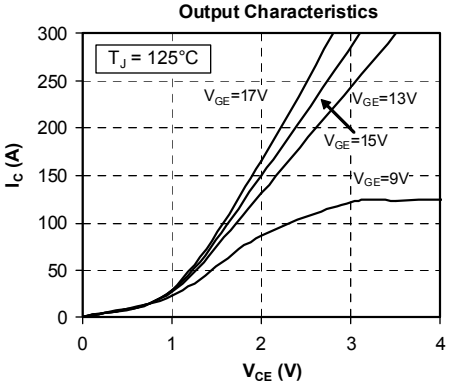


Typical Performance Curve

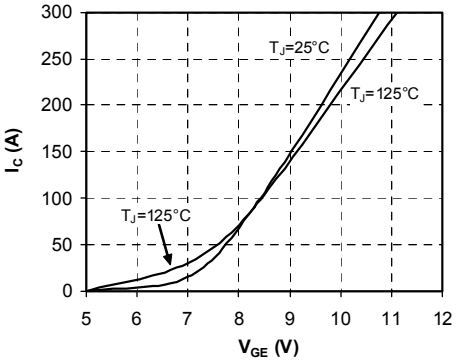
Output Characteristics (V_{GE}=15V)



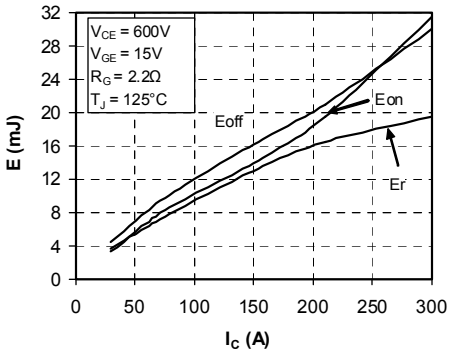
Output Characteristics



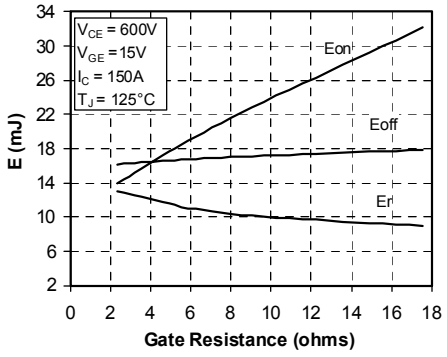
Transfert Characteristics



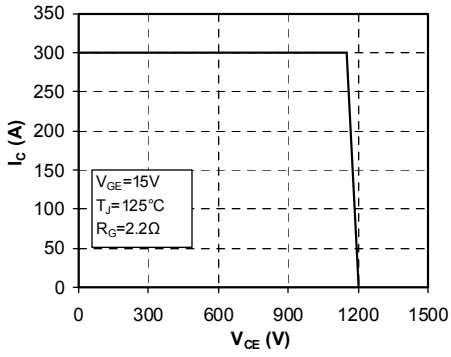
Energy losses vs Collector Current



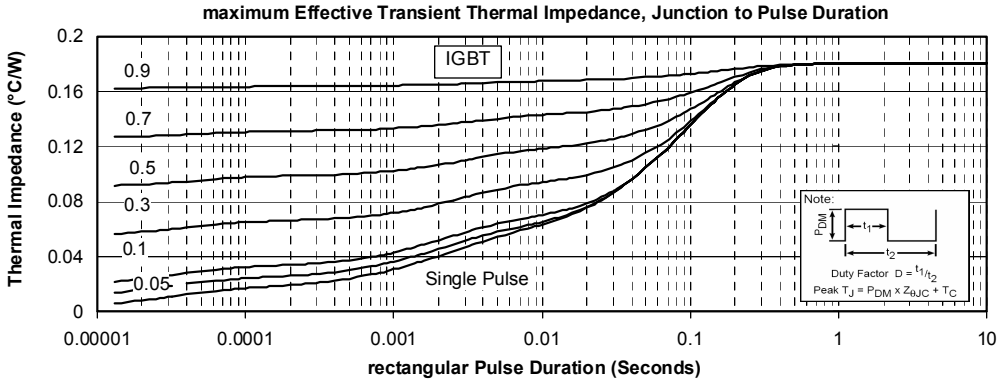
Switching Energy Losses vs Gate Resistance

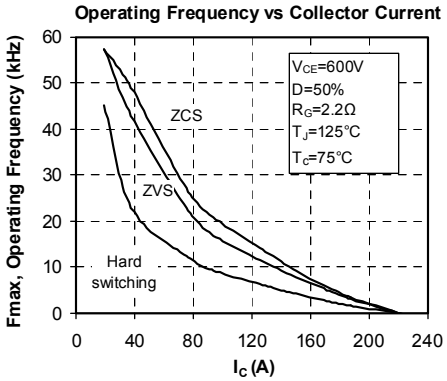


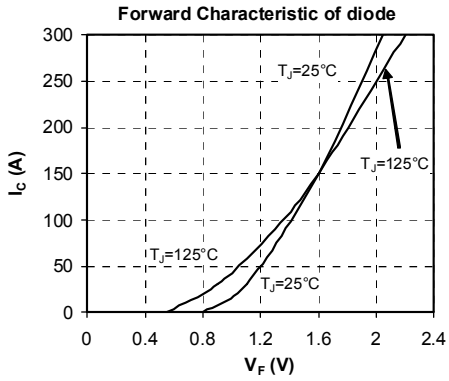
Reverse Bias Safe Operating Area

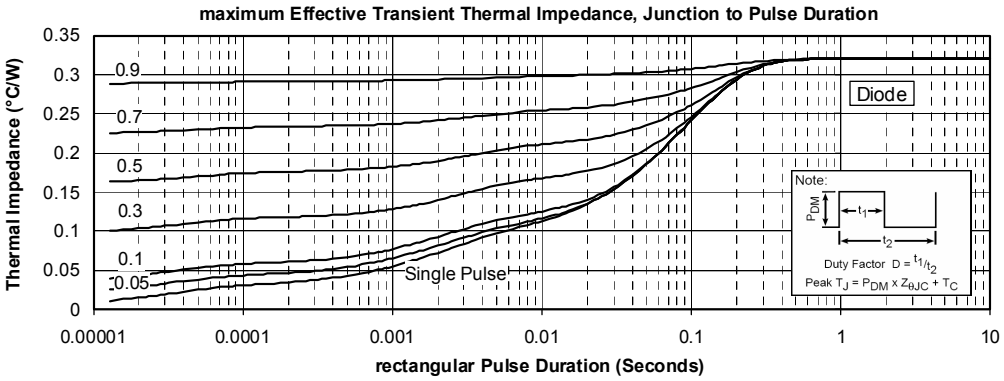


maximum Effective Transient Thermal Impedance, Junction to Pulse Duration









APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.